



# 29/09/03 G  
6/20/03  
500.36904X00  
C. Moore

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: MIURA, et al.  
Serial No.: 09/254,939  
Filed: March 17, 1999  
For: METHOD OF FABRICATING SEMICONDUCTOR DEVICE  
HAVING TRENCH ELEMENT SEPARATION STRUCTURE  
Group: 2814  
Examiner: Anh D. Mai

AMENDMENT

Mail Stop  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

June 5, 2003

Sir:

In response to the Office Action mailed March 5, 2003, please amend the  
above-identified application as follows:

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IN THE CLAIMS

Please amend the claims presently in the application as follows:

1. (Five Times Amended) A method of fabricating a semiconductor  
device comprising the steps of:
- (a) forming an oxidation prevention film on a circuit formation surface of a  
semiconductor substrate;
  - (b) forming a trench having a desired depth at a predetermined position of

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01 FC:1201  
02 FC:1202

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18.00 OP